

180V NPN MEDIUM POWER HIGH GAIN TRANSISTOR IN TO252

Features

- BV_{CEO} > 180V
- I_C = 0.5A high Continuous Collector Current
- I_{CM} = 1A Peak Pulse Current
- High gain device > 500 at I_C =100mA
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (23)
- Weight: 0.34 grams (approximate)

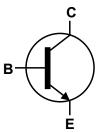
Applications

- Voltage Regulator Transistors
- Startup Switches
- Darlington Replacement
- DC Fans
- Relays and Solenoid Driving

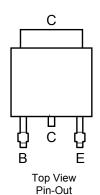
TO252 (DPAK)



Top View



Equivalent Circuit



Ordering Information (Note 4)

Product	Package	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DXT696BK-13	TO252 (DPAK)	DXT696B	13	16	2,500

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



O!! = Manufacturers' code marking
DXT 696B = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Digit of Year, (ex: 13 = 2013)
WW = Week Code 01 - 52



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	180	V
Collector-Emitter Voltage	V_{CEO}	180	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	Ic	0.5	Α
Peak Pulse Current	I _{CM}	1	Α
Peak Base Current	I _{BM}	0.5	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
	(Note 5)		3.9	
Power Dissipation	(Note 6)	P_{D}	2.1	W
	(Note 7)		1.6	
	(Note 5)		32	
Thermal Resistance, Junction to Ambient Air	(Note 6)	$R_{\theta JA}$	59	
	(Note 7)		80	°C/W
Thermal Resistance, Junction to Leads	(Note 8)	$R_{ heta JL}$	8.4	
Thermal Resistance, Junction to Case	(Note 9)	$R_{ heta JC}$	14.6	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

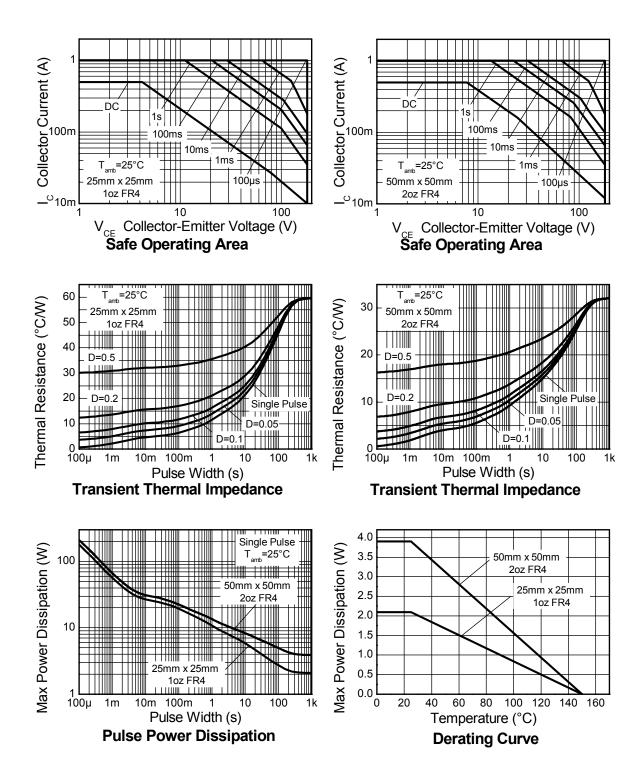
- 5. For a device mounted with the exposed collector pad on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- Same as note (5), except mounted on 25mm x 25mm 1oz copper.
- Same as note (5), except mounted on minimum recommended pad (MRP) layout.
- 8. Thermal resistance from junction to solder-point (on the exposed collector pad).
- 9. Thermal resistance from junction to the top of the case.
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

December 2013

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Thermal Characteristics and Derating Information





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

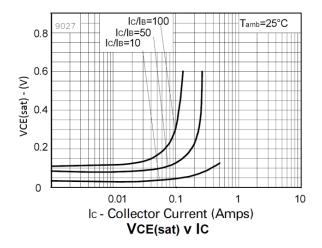
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	180	_	_	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	180	_	_	V	I _C = 1mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	_	_	V	I _E = 100μA
Collector-Base Cutoff Current	I _{CBO}	_	_	100	nA	V _{CB} = 140V
Emitter Cutoff Current	I _{EBO}	-	_	100	nA	V _{EB} = 5V
DC Current Gain (Note 11)	h	500	_	_		I _C = 100mA, V _{CE} = 5V
DC Current Gain (Note 11)	h _{FE}	150	_	_		I _C = 200mA, V _{CE} = 5V
	V _{CE(sat)}	_	_	200		$I_C = 50 \text{mA}, I_B = 0.5 \text{mA}$
Collector-Emitter Saturation Voltage (Note 11)		_	_	200	mV	$Ic = 100mA, I_B = 2.0mA$
		-	_	250		$I_C = 200 \text{mA}, I_B = 5.0 \text{mA}$
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	-	_	900	mV	I _C = 200mA, I _B = 5mA
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	_	_	900	mV	I _C = 200mA, V _{CE} = 5V
Input Capacitance	C _{ibo}	_	200	_	pF	V _{EB} = 0.5V, f = 1MHz
Output Capacitance	C _{obo}	_	6	_	pF	V _{CE} = 10V, f = 1MHz
Current Gain-Bandwidth Product	f _T	70	_	_	MHz	V _{CE} = 5V, I _C = 50mA, f=50MHz
Turn-On Time	t _{on}		80	_	ns	V _{CC} = 50V, I _C = 100mA
Turn-Off Time	t _{off}		4,400	_	ns	$I_{B1} = -I_{B2} = 10 \text{mA}$

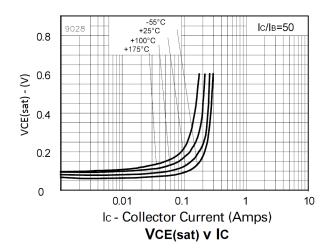
Note:

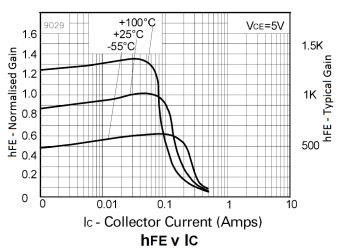
11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

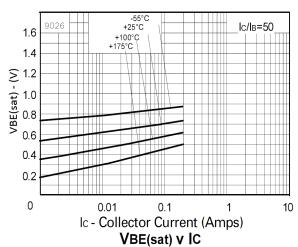


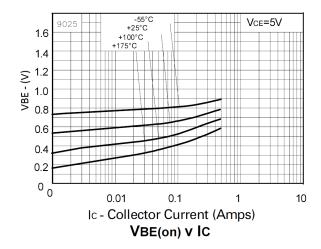
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)







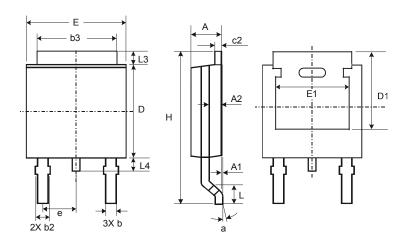






Package Outline Dimensions

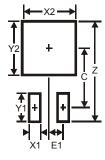
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



TO252				
Dim	Min	Max	Тур	
Α	2.19	2.39	2.29	
A 1	0.00	0.13	0.08	
A2	0.97	1.17	1.07	
b	0.64	0.88	0.783	
b2	0.76	1.14	0.95	
b3	5.21	5.46	5.33	
c2	0.45	0.58	0.531	
D	6.00	6.20	6.10	
D1	5.21	_	_	
е	_	_	2.286	
Е	6.45	6.70	6.58	
E1	4.32	_	_	
Н	9.40	10.41	9.91	
L	1.40	1.78	1.59	
L3	0.88	1.27	1.08	
L4	0.64	1.02	0.83	
а	0°	10°	_	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
С	6.9
E1	2.3

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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